

PMV20XNER Datasheet



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DiGi Electronics Part Number PMV20XNER-DG

Manufacturer Nexperia USA Inc.

Manufacturer Product Number PMV20XNER

Description MOSFET N-CH 30V 5.7A TO236AB

Detailed Description N-Channel 30 V 5.7A (Ta) 510mW (Ta), 6.94W (Tc) S

urface Mount TO-236AB



Tel: +00 852-30501935

RFQ Email: Info@DiGi-Electronics.com

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Purchase and inquiry

Manufacturer Product Number:	Manufacturer:
PMV20XNER	Nexperia USA Inc.
Series:	Product Status:
	Active
FET Type:	Technology:
N-Channel	MOSFET (Metal Oxide)
Drain to Source Voltage (Vdss):	Current - Continuous Drain (Id) @ 25°C:
30 V	5.7A (Ta)
Drive Voltage (Max Rds On, Min Rds On):	Rds On (Max) @ ld, Vgs:
1.8V, 4.5V	23mOhm @ 5.7A, 4.5V
Vgs(th) (Max) @ Id:	Gate Charge (Qg) (Max) @ Vgs:
900mV @ 250μA	18.6 nC @ 4.5 V
Vgs (Max):	Input Capacitance (Ciss) (Max) @ Vds:
±12V	1150 pF @ 15 V
FET Feature:	Power Dissipation (Max):
	510mW (Ta), 6.94W (Tc)
Operating Temperature:	Mounting Type:
-55°C ~ 150°C (TJ)	Surface Mount
Supplier Device Package:	Package / Case:
TO-236AB	TO-236-3, SC-59, SOT-23-3
Base Product Number:	
PMV20	

Environmental & Export classification

8541.29.0095

RoHS Status:	Moisture Sensitivity Level (MSL):
ROHS3 Compliant	1 (Unlimited)
REACH Status:	ECCN:
REACH Unaffected	EAR99
HTSUS:	



PMV20XNE

30 V, N-channel Trench MOSFET

10 November 2014

Product data sheet

1. General description

N-channel enhancement mode Field-Effect Transistor (FET) in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

2. Features and benefits

- Trench MOSFET technology
- Low threshold voltage
- Enhanced power dissipation capability of 1200 mW
- ElectroStatic Discharge (ESD) protection: 2 kV HBM

3. Applications

- Relay driver
- High-speed line driver
- Low-side load switch
- Switching circuits

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	-	30	V
V_{GS}	gate-source voltage			-12	-	12	V
I _D	drain current	V _{GS} = 4.5 V; T _{amb} = 25 °C; t ≤ 5 s	[1]	-	-	7.2	Α
Static characteristics							,
R _{DSon}	drain-source on-state resistance	V_{GS} = 4.5 V; I_{D} = 5.7 A; T_{j} = 25 °C		-	19	23	mΩ

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².



30 V, N-channel Trench MOSFET

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	3	D I
2	S	source		
3	D	drain	1 2 TO-236AB (SOT23)	G S 017aaa255

6. Ordering information

Table 3. Ordering information

Type number	Package			
	Name	Description	Version	
PMV20XNE	TO-236AB	plastic surface-mounted package; 3 leads	SOT23	

7. Marking

Table 4. Marking codes

Type number	Marking code [1]
PMV20XNE	%G9

[1] % = placeholder for manufacturing site code

30 V, N-channel Trench MOSFET

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit	
V _{DS}	drain-source voltage	T _j = 25 °C		-	30	V	
V_{GS}	gate-source voltage			-12	12	V	
I _D	drain current	V _{GS} = 4.5 V; T _{amb} = 25 °C; t ≤ 5 s	[1]	-	7.2	Α	
		V _{GS} = 4.5 V; T _{amb} = 25 °C	[1]	-	5.7	Α	
		V _{GS} = 4.5 V; T _{amb} = 100 °C	[1]	-	3.6	Α	
I _{DM}	peak drain current	T_{amb} = 25 °C; single pulse; $t_p \le 10$ μs		-	24	Α	
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2]	-	510	mW	
			[1]	-	1200	mW	
		T _{sp} = 25 °C		-	6940	mW	
Tj	junction temperature			-55	150	°C	
T _{amb}	ambient temperature			-55	150	°C	
T _{stg}	storage temperature			-65	150	°C	
Source-drain o	Source-drain diode						
I _S	source current	T _{amb} = 25 °C	[1]	-	1.2	Α	

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².

^[2] Device mounted on an FR4 Printed Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

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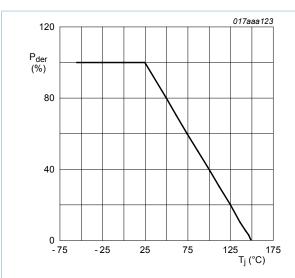


Fig. 1. Normalized total power dissipation as a function of junction temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$

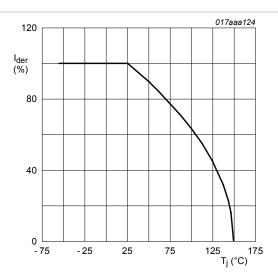
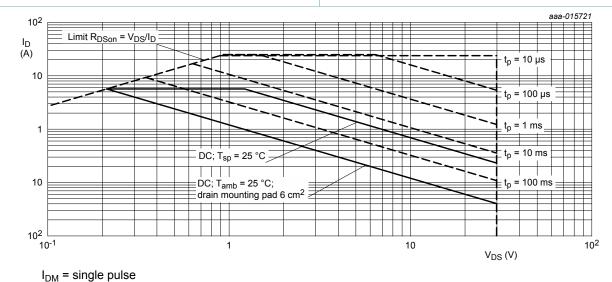


Fig. 2. Normalized continuous drain current as a function of junction temperature

$$I_{der} = \frac{I_D}{I_{D(25^{\circ}C)}} \times 100 \%$$



IDM Single pales

Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drainsource voltage

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)}	thermal resistance	in free air	[1]	-	208	245	K/W
	from junction to ambient		[2]	-	88	104	K/W
		in free air; t ≤ 5 s	[2]	-	55	65	K/W

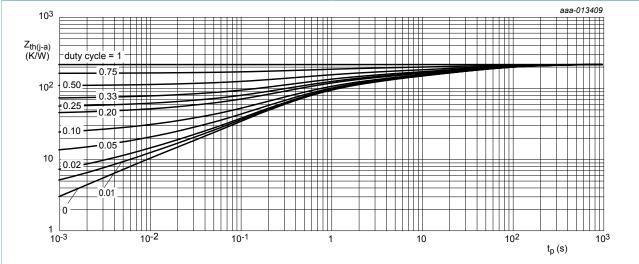
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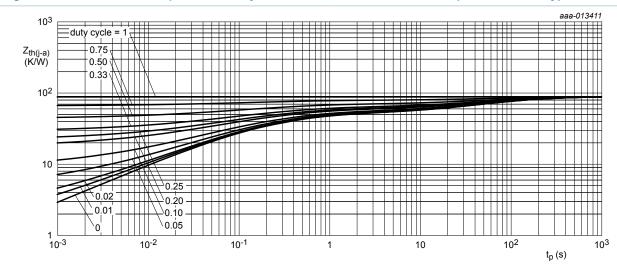
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-sp)}	thermal resistance from junction to solder point		-	13	18	K/W

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm².



FR4 PCB, standard footprint

Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, mounting pad for drain 6 cm²

Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

30 V, N-channel Trench MOSFET

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	30	-	-	V
V_{GSth}	gate-source threshold voltage	$I_D = 250 \mu A; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$	0.4	0.65	0.9	V
I _{DSS}	drain leakage current	V _{DS} = 30 V; V _{GS} = 0 V; T _j = 25 °C	-	-	1	μΑ
I _{GSS}	gate leakage current	V _{GS} = 8 V; V _{DS} = 0 V; T _j = 25 °C	-	-	10	μA
	V _{GS} = -8 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-10	μA	
R _{DSon}	drain-source on-state	V _{GS} = 4.5 V; I _D = 5.7 A; T _j = 25 °C	-	19	23	mΩ
	resistance	V _{GS} = 4.5 V; I _D = 5.7 A; T _j = 150 °C	-	31	37	mΩ
		V_{GS} = 2.5 V; I_D = 5 A; T_j = 25 °C	-	22	30	mΩ
	V _{GS} = 1.8 V; I _D = 1.9 A; T _j = 25 °C	-	27	38	mΩ	
9 _{fs}	forward transconductance	V_{DS} = 10 V; I_D = 2 A; T_j = 25 °C	-	11	-	S
R _G	gate resistance	f = 1 MHz; T _j = 25 °C	-	1.8	-	Ω
Dynamic ch	aracteristics					
Q _{G(tot)}	total gate charge	V_{DS} = 10 V; I_{D} = 5 A; V_{GS} = 4.5 V;	-	12.4	18.6	nC
Q_{GS}	gate-source charge	T _j = 25 °C	-	1.2	-	nC
Q_{GD}	gate-drain charge		-	2.1	-	nC
C _{iss}	input capacitance	V _{DS} = 15 V; f = 1 MHz; V _{GS} = 0 V;	-	1150	-	pF
C _{oss}	output capacitance	T _j = 25 °C	-	110	-	pF
C _{rss}	reverse transfer capacitance		-	85	-	pF
t _{d(on)}	turn-on delay time	V _{DS} = 15 V; I _D = 5 A; V _{GS} = 4.5 V;	-	8	-	ns
t _r	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 °C$	-	17	-	ns
t _{d(off)}	turn-off delay time		-	33	-	ns
t _f	fall time		-	32	-	ns
Source-drai	in diode		<u> </u>		1	
V _{SD}	source-drain voltage	I _S = 1.2 A; V _{GS} = 0 V; T _i = 25 °C	-	0.7	1.2	V

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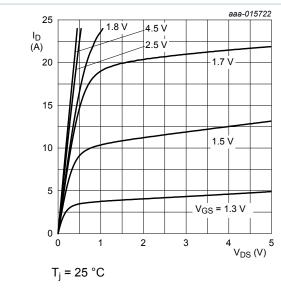


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

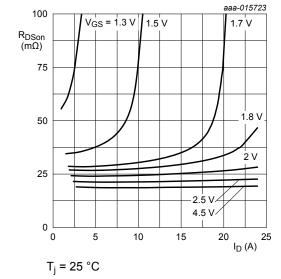


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

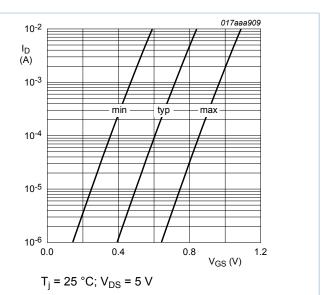


Fig. 7. Subthreshold drain current as a function of gate-source voltage

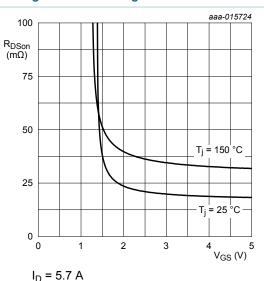


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

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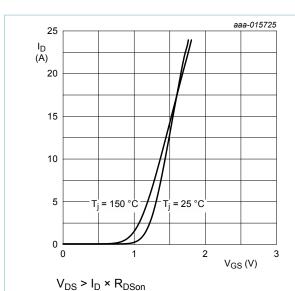


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

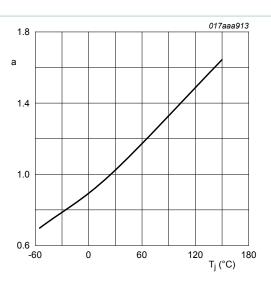


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$

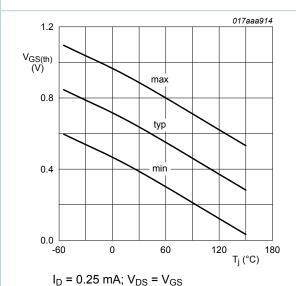


Fig. 12. Gate-source threshold voltage as a function of junction temperature

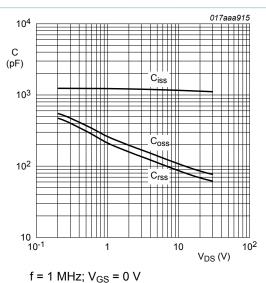


Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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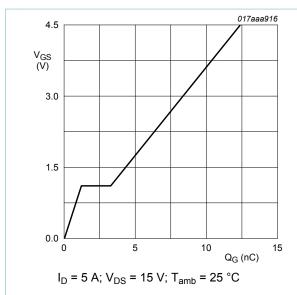


Fig. 14. Gate-source voltage as a function of gate charge; typical values

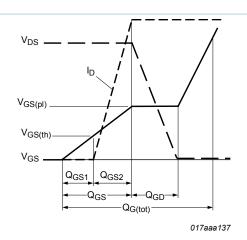


Fig. 15. MOSFET transistor: Gate charge waveform definitions

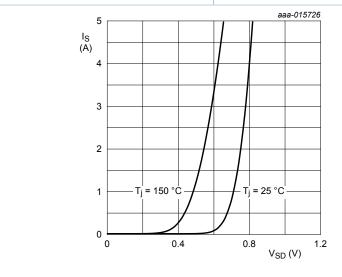
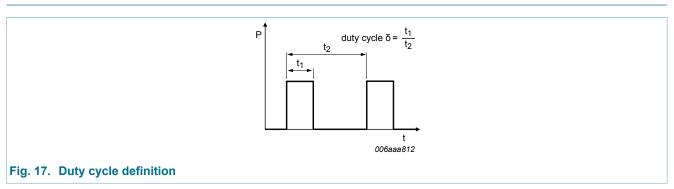


Fig. 16. Source current as a function of source-drain voltage; typical values

11. Test information

 $V_{GS} = 0 V$

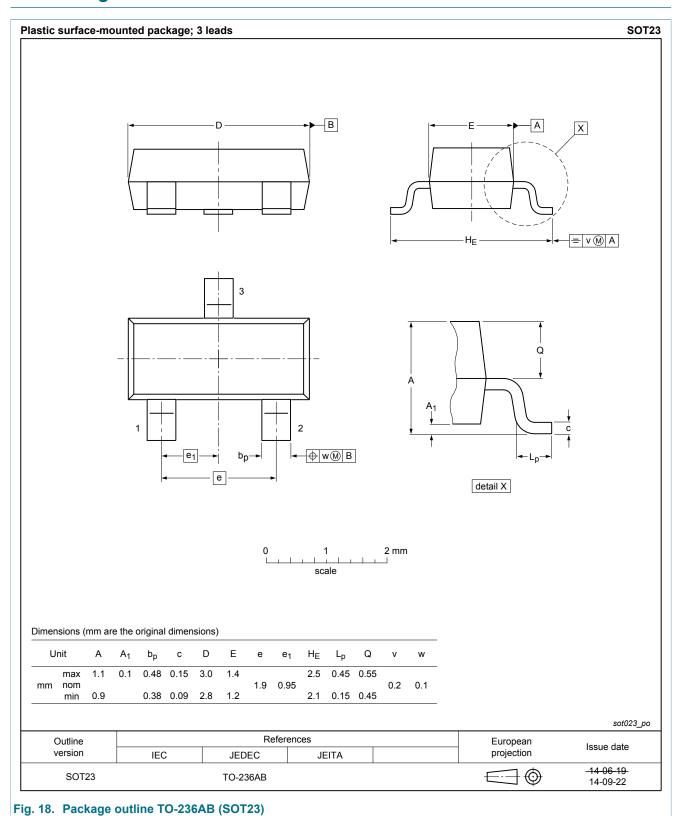


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12. Package outline

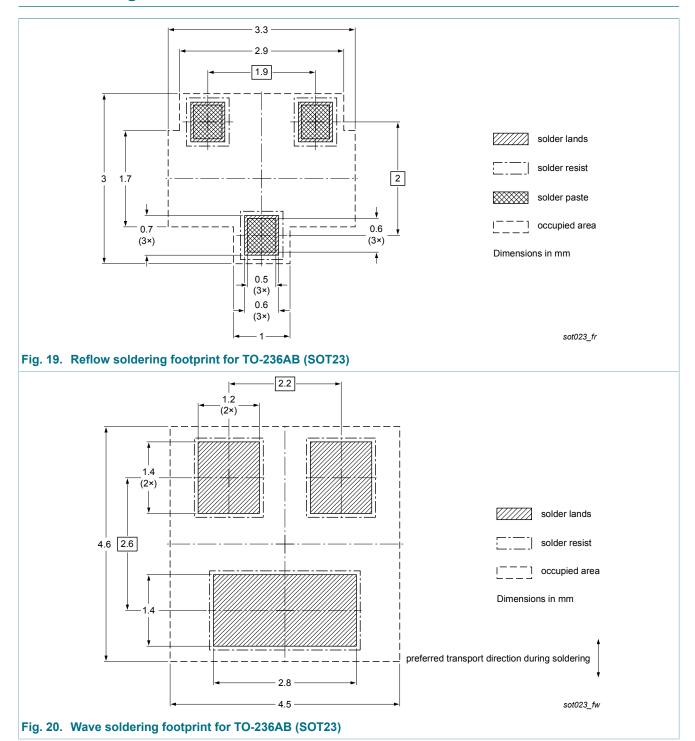


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13. Soldering



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14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMV20XNE v.1	20141110	Product data sheet	-	-

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15. Legal information

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Document status [1][2]	Product status [3]	Definition
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Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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